



N 沟道增强型场效应晶体管  
N-CHANNEL MOSFET  
FHP830B

主要参数 MAIN CHARACTERISTICS

ID	5A
VDSS	500V
Rdson-typ ( @Vgs=10V)	1.35Ω
Qg-typ	26nC

用途 APPLICATIONS

高频开关电源	High efficiency switch mode power supplies
电子镇流器	Electronic ballast
逆变电源	Power management for inverter systems

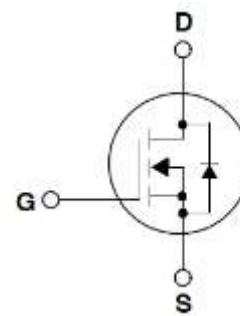
封装形式 Package



产品特性 FEATURES

低栅极电荷	Low gate charge
低 Crss (典型值 17pF)	Low Crss (typical 17pF)
开关速度快	Fast switching
100%经过雪崩测试	100% avalanche tested
高抗 dv/dt 能力	Improved dv/dt capability
RoHS 产品	RoHS product

等效电路 Equivalent Circuit



绝对最大额定值 ABSOLUTE RATINGS (Tc=25°C)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
		FHP830B	
最高漏极-源极直流电压 Drain-Source Voltage	VDS	500	V
连续漏极电流* Drain Current -continuous *	ID (TC=25°C)	5	A
	ID (TC=100°C)	3	A
最大脉冲漏极电流 (注 1) Drain Current – pulse (note 1)	IDM	20	A
最高栅源电压 Gate-Source Voltage	VGS	±30	V
单脉冲雪崩能量 (注 2) Single Pulsed Avalanche Energy (note 2)	EAS	280	mJ
雪崩电流 (注 1) Avalanche Current (note 1)	IAR	5	A
重复雪崩能量 (注 1) Repetitive Avalanche Current (note 1)	EAR	6.5	mJ
二极管反向恢复最大电压变化速率 (注 3) Peak Diode Recovery dv/dt (note 3)	dv/dt	4.5	V/ns
耗散功率 Power Dissipation	PD (TC=25°C)	74	W
	-Derate above 25°C	0.54	W/°C
最高结温及存储温度 Operating and Storage Temperature Range	TJ, TSTG	150, -55 to 150	°C
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	TL	300	°C

\*漏极电流由最高结温限制

\*Drain current limited by maximum junction temperature

## 电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
<b>关态特性 Off –Characteristics</b>						
漏-源击穿电压 Drain-Source Voltage	BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	500	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA, referenced to 25°C	-	0.5	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V, T <sub>C</sub> =25°C	-	-	1	μA
		V <sub>DS</sub> =400V, T <sub>C</sub> =125°C	-	-	10	μA
栅极体漏电流 Gate-body leakage current	I <sub>GSS</sub> (F/R)	V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V	-	-	±100	nA
<b>通态特性 On-Characteristics</b>						
阈值电压 Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	2.0	-	4.0	V
静态导通电阻 Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V , I <sub>D</sub> =2.5A	-	1.35	1.5	Ω
正向跨导 Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 40V, I <sub>D</sub> =2.5A (note 4)	2.4	-	-	S
<b>动态特性 Dynamic Characteristics</b>						
输入电容 Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	560	-	pF
输出电容 Output capacitance	C <sub>oss</sub>		-	45	-	
反向传输电容 Reverse transfer capacitance	C <sub>rss</sub>		-	17	-	
<b>开关特性 Switching Characteristics</b>						
延迟时间 Turn-On delay time	t <sub>d(on)</sub>	V <sub>DS</sub> =250V, I <sub>D</sub> =5A, R <sub>G</sub> =20Ω V <sub>GS</sub> =10V (note 4, 5)	-	10	-	ns
上升时间 Turn-On rise time	t <sub>r</sub>		-	15	-	ns
延迟时间 Turn-Off delay time	t <sub>d(off)</sub>		-	20	-	ns
下降时间 Turn-Off Fall time	t <sub>f</sub>		-	16	-	ns
栅极电荷总量 Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =400V , I <sub>D</sub> =10A , V <sub>GS</sub> =10V (note 4, 5)	-	26	-	nC
栅-源电荷 Gate-Source charge	Q <sub>gs</sub>		-	4	-	nC
栅-漏电荷 Gate-Drain charge	Q <sub>gd</sub>		-	15	-	nC
<b>漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings</b>						
正向最大连续电流 Maximum Continuous Drain-Source Diode Forward Current		I <sub>S</sub>	-	-	5	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current		I <sub>SM</sub>	-	-	20	A
正向压降 Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =5A	-	-	1.4	V
反向恢复时间 Reverse recovery time	t <sub>rr</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =5A ,dI <sub>F</sub> /dt=100A/μs (note 4)	-	220	-	ns
反向恢复电荷 Reverse recovery charge	Q <sub>rr</sub>		-	1.0	-	μC

## 热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	FHP830B	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	Rth(j-c)	1.69	°C/W
结到环境的热阻 Thermal Resistance, Junction to Ambient	Rth(j-A)	62.5	°C/W

### 注释:

- 1: 脉冲宽度由最高结温限制
- 2: L=24mH, IAS=5A, VDD=50V, RG=25 Ω, 起始结温 TJ=25°C
- 3: ISD ≤5A, di/dt ≤100A/μs, VDD≤BV<sub>DSS</sub>, 起始结温 TJ=25°C
- 4: 脉冲测试: 脉冲宽度 ≤300μs, 占空比≤2%
- 5: 基本与工作温度无关

### Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: L=24mH, ID=5A, VDD=50V, RG=25 Ω, Start TJ=25°C;
- 3: ISD ≤5A, di/dt ≤100A/μs, VDD≤BV<sub>DSS</sub>, Starting TJ=25°C
- 4: Pulse Test: Pulse Width ≤300μs, Duty Cycle≤2%
- 5: Essentially independent of operating temperature

# 特性曲线

## (ELECTRICAL CHARACTERISTICS (curves))

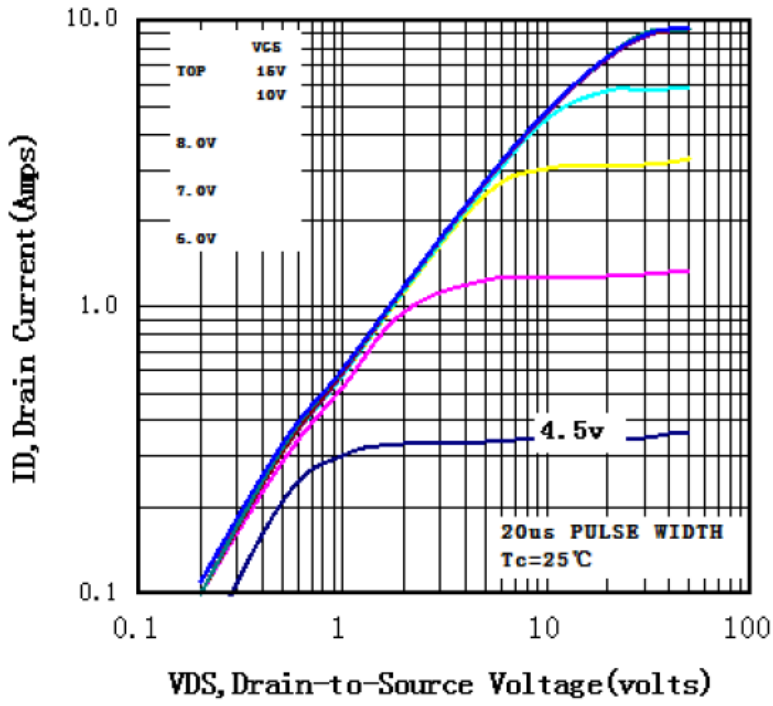


图 1 输出特性曲线, Tc=25°C

Fig1 Typical Output Characteristics, Tc=25°C

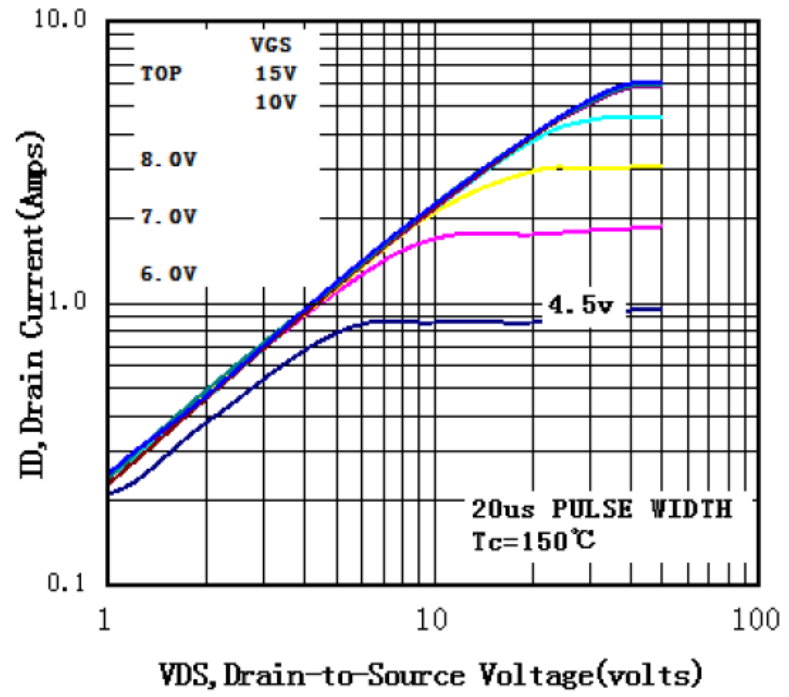


图 2 输出特性曲线, Tc=150°C

Fig2 Typical Output Characteristics, Tc=150°C

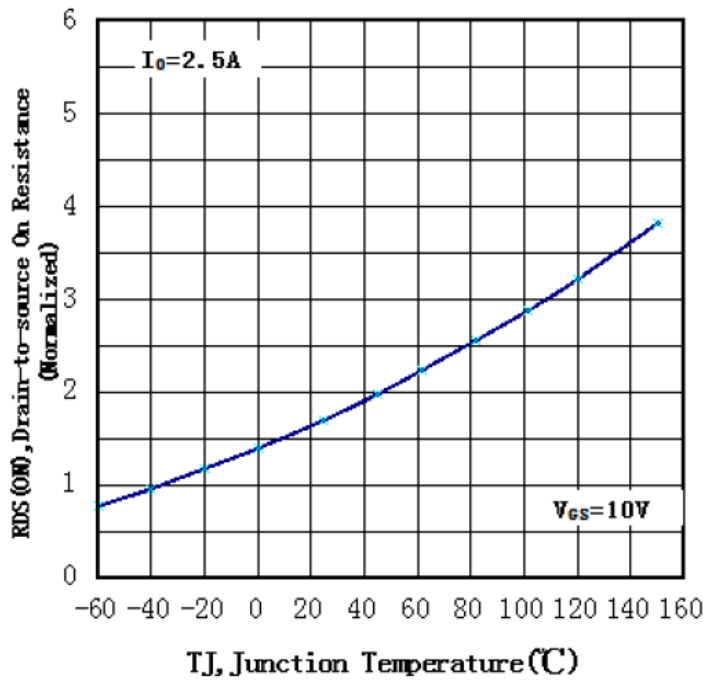


图 3 归一化导通电阻与温度曲线

Fig3 Normalized Resistance Vs. Temperature

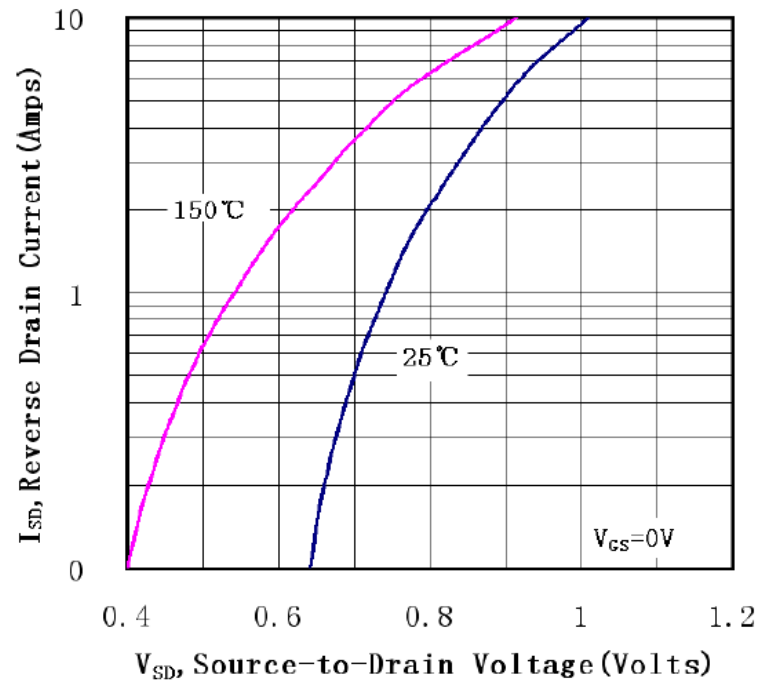


图 4 二极管正向电压曲线

Fig4 Typical Source-Drain Diode Forward Voltage

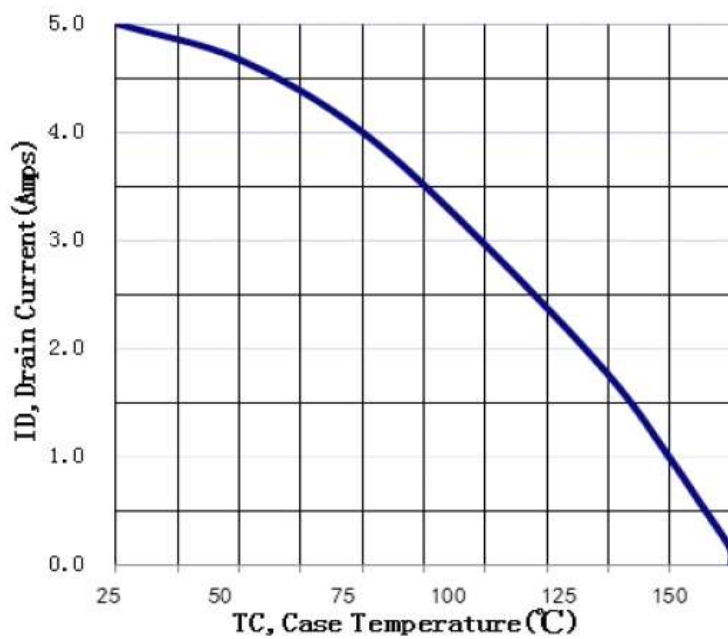


图 5 最大漏极电流与壳温曲线

Fig5 Maximum Drain Current Vs. Case Temperature

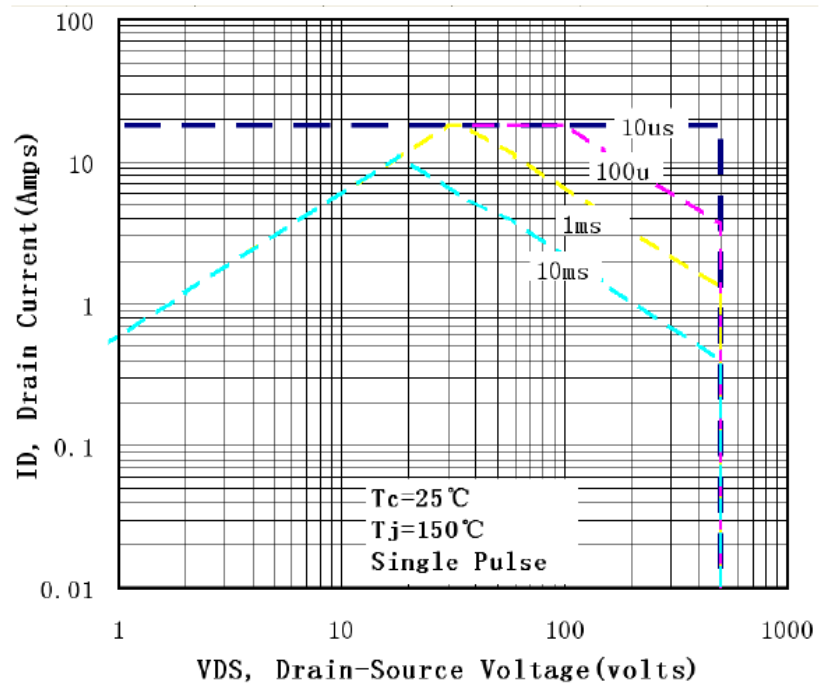
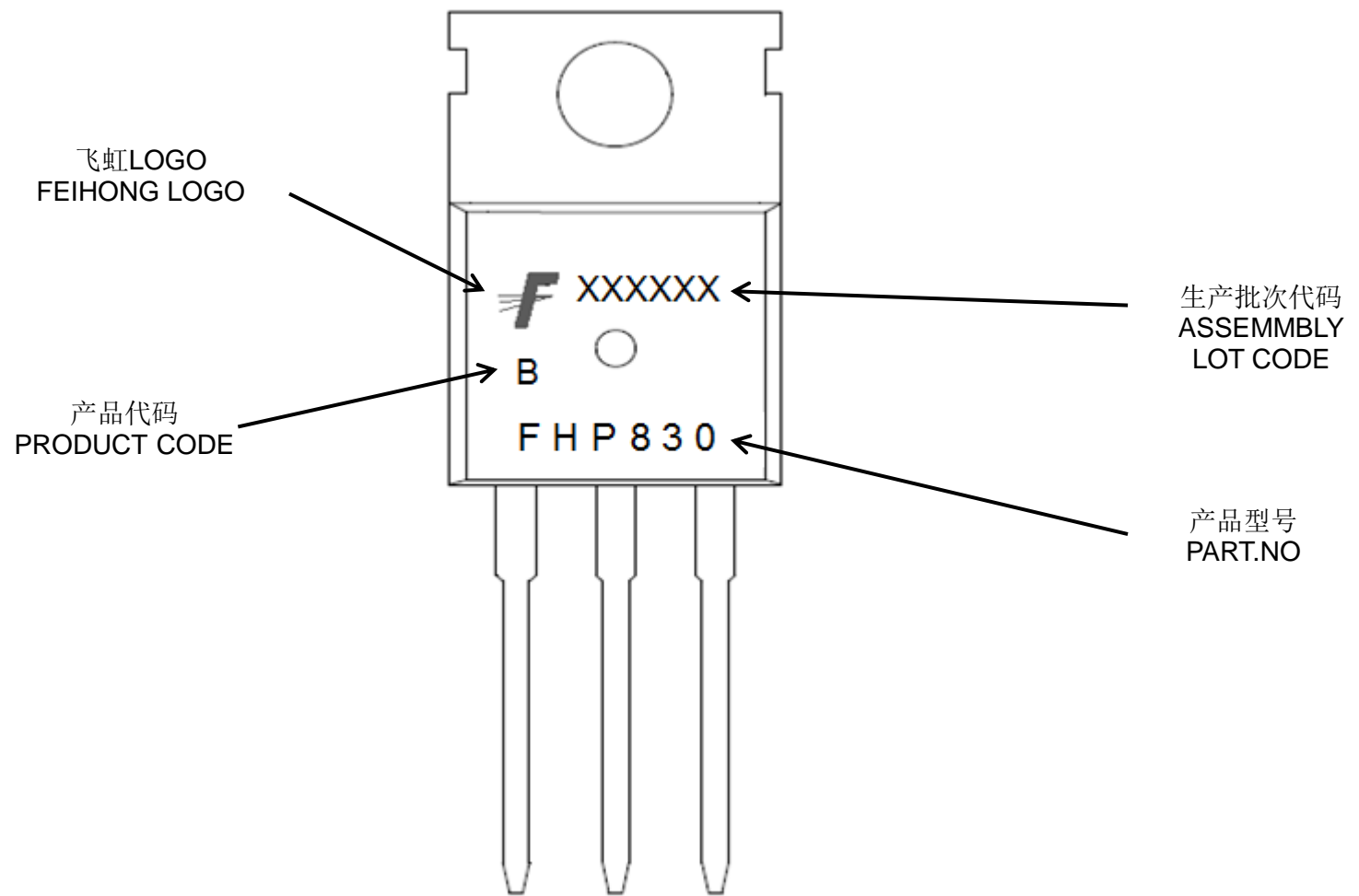


图 6 最大安全工作区曲线

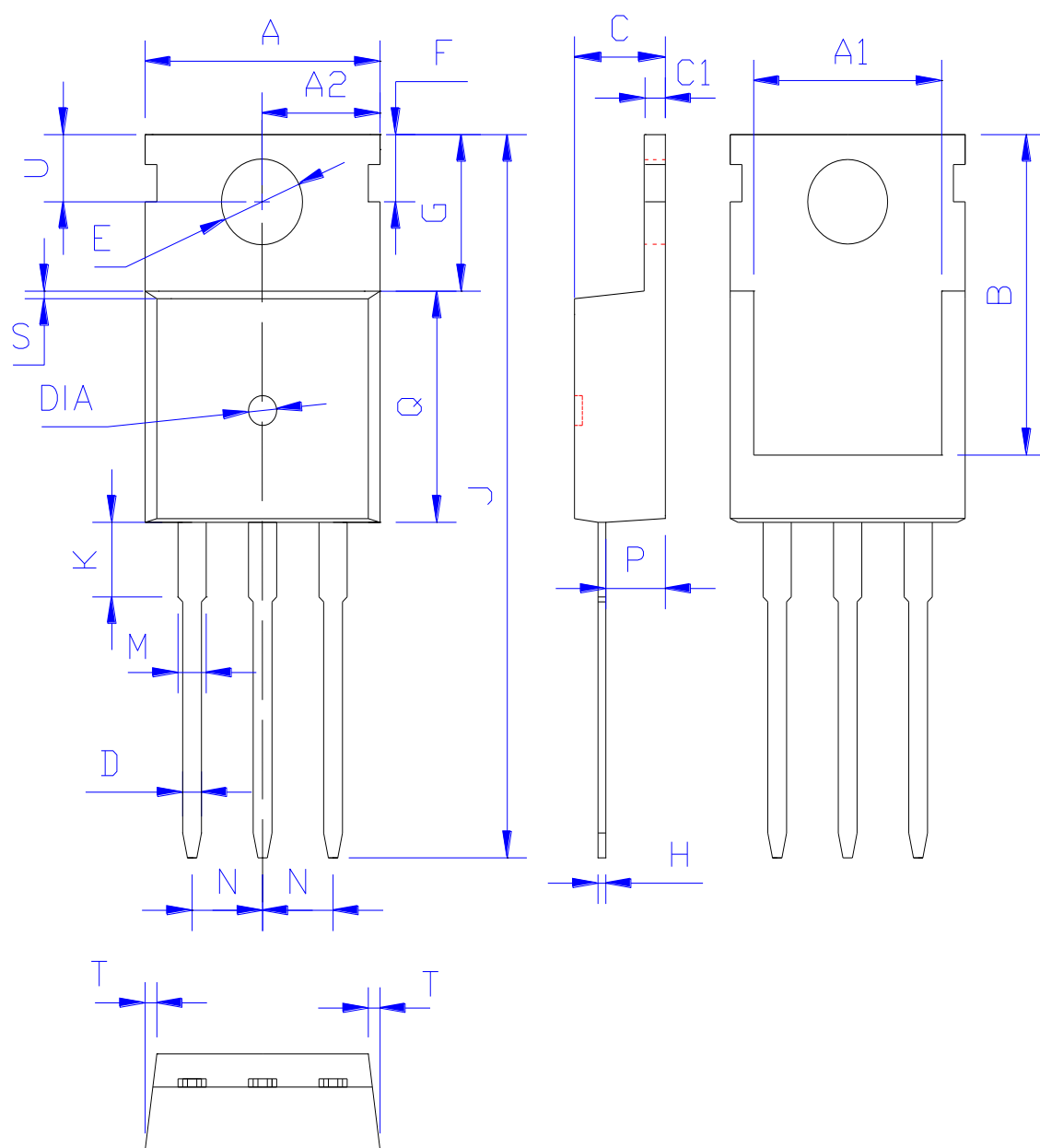
Fig6 Maximum Safe Operating Area

印记 Marking:



外形尺寸:  
Package Dimension:

TO-220



DIM	MILLIMETERS
A	10.00±0.30
A1	8.00±0.30
A2	5.00±0.30
B	13.20±0.40
C	4.50±0.20
C1	1.30±0.20
D	0.80±0.20
E	3.60±0.20
F	3.00±0.30
G	6.60±0.40
H	0.50±0.20
J	28.88±0.50
K	3.00±0.30
M	1.30±0.30
N	Typical 2.54
P	2.40±0.40
Q	9.20±0.40
S	0.25±0.15
T	0.25±0.15
U	2.80±0.30
DIA	宽 1.50±0.10 深 0.50 MAX

(Units: mm)